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# LM136A-2.5/LM136-2.5QML Reference Diode

## General Description

The LM136A-2.5/LM136-2.5 integrated circuit is a precision 2.5V shunt regulator diode. This monolithic IC voltage reference operates as a low-temperature-coefficient 2.5V zener with 0.2Ω dynamic impedance. A third terminal on the LM136-2.5 allows the reference voltage and temperature coefficient to be trimmed easily.

The LM136-2.5 is useful as a precision 2.5V low voltage reference for digital voltmeters, power supplies or op amp circuitry. The 2.5V make it convenient to obtain a stable reference from 5V logic supplies. Further, since the LM136-2.5 operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

## Features

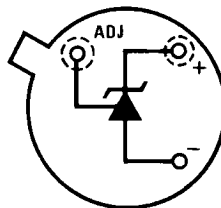
- Available with radiation guarantee  
— Total Ionizing Dose 100 krad(Si)
- Low temperature coefficient
- Wide operating current of 400 μA to 10 mA
- Guaranteed temperature stability
- Easily trimmed for minimum temperature drift
- Fast turn-on
- 3-lead transistor package

## Ordering Information

NS Part Number	SMD Part Number	NS Package Number	Package Description
LM136H-2.5/883		H03H	T0-46, 3LD Metal Can
LM136AH-2.5-SMD	8418003XA	H03H	T0-46, 3LD Metal Can
LM136AH-2.5/883		H03H	T0-46, 3LD Metal Can
LM136AH-2.5RQV (Note 5)	5962R0050101VXA 100 krad(Si)	H03H	T0-46, 3LD Metal Can
LM136AH-2.5RLQV (Note 6)	5962R0050102VXA 100 krad(Si)	H03H	T0-46, 3LD Metal Can

## Connection Diagram

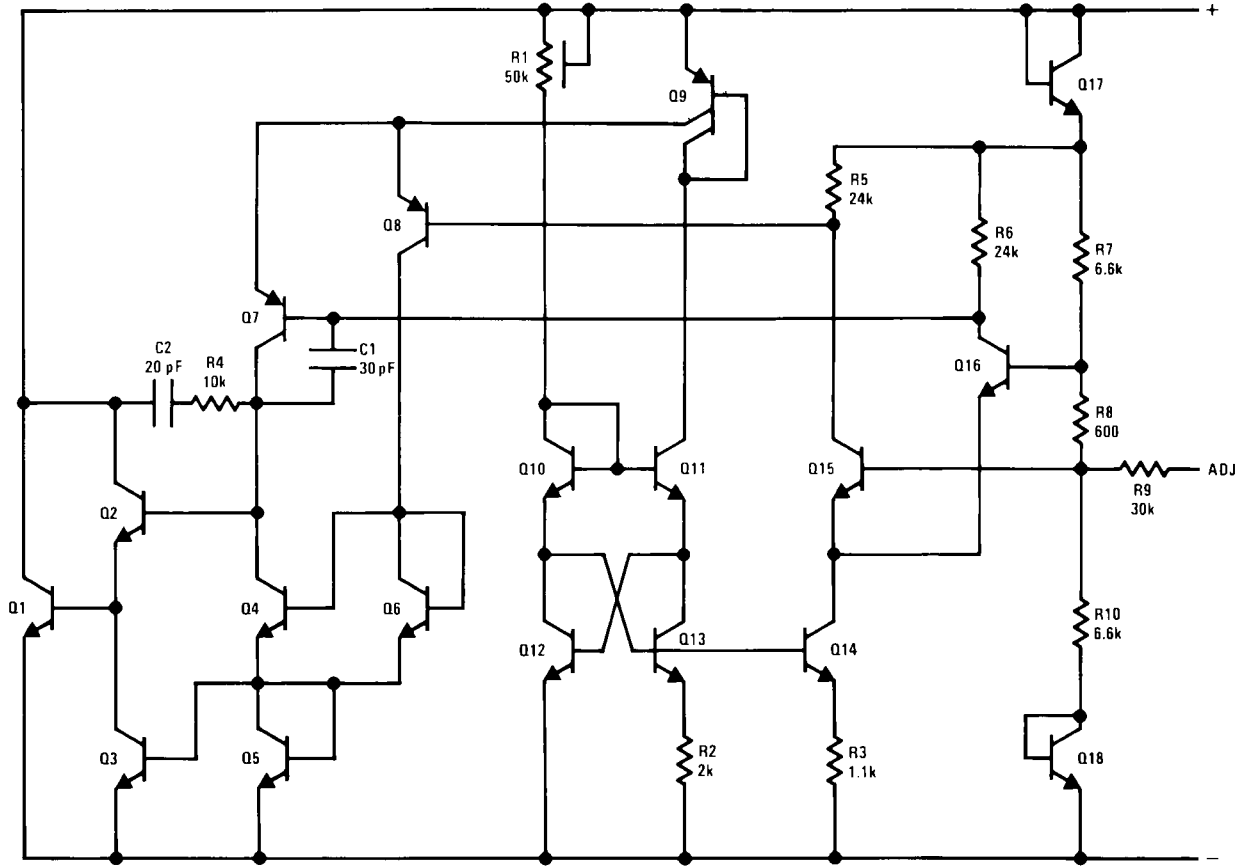
TO-46  
Metal Can Package



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Bottom View  
See NS Package Number H03H

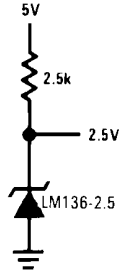
# Schematic Diagram



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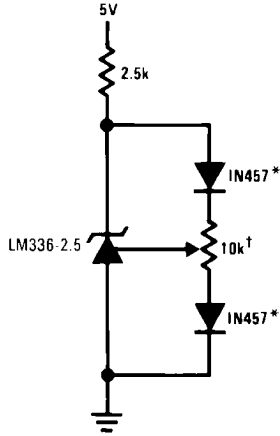
# Typical Applications

**2.5V Reference**



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**2.5V Reference with Minimum Temperature Coefficient**

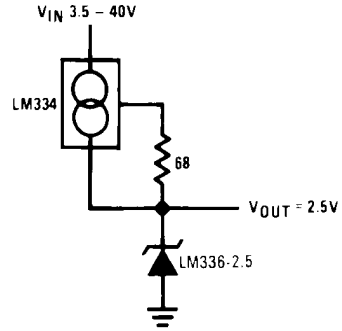


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†Adjust to 2.490V

\*Any silicon signal diode

**Wide Input Range Reference**



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## Absolute Maximum Ratings (Note 1)

Reverse Current	15 mA
Forward Current	10 mA
Storage Temperature	$-60^{\circ}\text{C} \leq T_A \leq +150^{\circ}\text{C}$
Operating Temperature Range (Note 2)	$-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$
Maximum Junction Temperature ( $T_J$ )(Note 2)	$+150^{\circ}\text{C}$
Lead Temperature (Soldering 10 seconds)	$300^{\circ}\text{C}$
Thermal Resistance	
$\theta_{JA}$	
Still Air Flow	$354^{\circ}\text{C/W}$
500LF/Min Air Flow	$77^{\circ}\text{C/W}$
$\theta_{JC}$	$46^{\circ}\text{C/W}$
ESD Rating (Note 3)	1,000V

## Quality Conformance Inspection

Mil-Std-883, Method 5005 - Group A

Subgroup	Description	Temp °C
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55
12	Settling time at	25
13	Settling time at	125
14	Settling time at	-55

## LM136-2.5 Electrical Characteristics

### DC Parameters

The following conditions apply, unless otherwise specified.  $I_R = 1\text{mA}$

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
$I_{Adj}$	Adjust Current	$V_{Adj} = 0.7\text{V}$		-125	+125	$\mu\text{A}$	1, 2, 3
$\Delta V_Z$	Delta Zener Voltage	$0.4\text{mA} \leq I_Z \leq 10\text{mA}$			6.0	mV	1
					10	mV	2, 3
$V_Z$	Zener Voltage	$V_{Adj} = \text{Open}$		2.44	2.54	V	1
				2.42	2.56	V	2, 3
		$V_{Adj} = 0.7\text{V}$		2.39	2.49	V	1
				2.29	2.49	V	2, 3
	$V_{Adj} = 1.9\text{V}$		2.49	2.69	V	1, 2, 3	
$Z_{RD}$	Reverse Dynamic Impedance		(Note 4)		1.0	$\Omega$	1, 2, 3
$V_{Stab}$	Temperature Stability	$V_Z = \text{Adjusted to } 2.490\text{V}$			18	mV	2, 3

## LM136A-2.5 Electrical Characteristics

### DC Parameters

The following conditions apply, unless otherwise specified.  $I_R = 1\text{ mA}$

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
$I_{Adj}$	Adjust Current	$V_{Adj} = 0.7\text{V}$		-125	+125	$\mu\text{A}$	1, 2, 3
$\Delta V_Z$	Delta Zener Voltage	$0.4\text{mA} \leq I_Z \leq 10\text{ mA}$			6.0	mV	1
					10	mV	2, 3
$V_Z$	Zener Voltage	$V_{Adj} = \text{Open}$		2.465	2.515	V	1
				2.44	2.54	V	2, 3
		$V_{Adj} = 0.7\text{V}$		2.39	2.49	V	1
				2.29	2.49	V	2, 3
$V_{Adj} = 1.9\text{V}$		2.49	2.69	V	1, 2, 3		
$Z_{RD}$	Reverse Dynamic Impedance		(Note 4)		0.6	$\Omega$	1
			(Note 4)		1.0	$\Omega$	2, 3
$V_{Stab}$	Temperature Stability	$V_Z = \text{Adjusted to } 2.490\text{V}$			18	mV	2, 3

### DC Drift Parameters

Delta calculations are performed on QMLV devices at Group B, Subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub-groups
$V_Z$	Zener Voltage	$V_{Adj} = \text{Open}$		-10	+10	mV	1
		$V_{Adj} = 0.7\text{V}$		-10	+10	mV	1
		$V_{Adj} = 1.9\text{V}$		-10	+10	mV	1

**Note 1:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

**Note 2:** The maximum power dissipation must be derated at elevated temperatures and is dictated by  $T_{Jmax}$  (maximum junction temperature),  $\theta_{JA}$  (package junction to ambient thermal resistance), and  $T_A$  (ambient temperature). The maximum allowable power dissipation at any temperature is  $P_{Dmax} = (T_{Jmax} - T_A) / \theta_{JA}$  or the number given in the Absolute Maximum Ratings, whichever is lower.

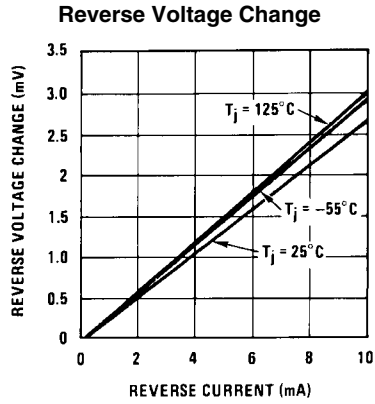
**Note 3:** Human body model, 1.5K $\Omega$  in series with 100pF.

**Note 4:** Parameter tested go-no-go only.

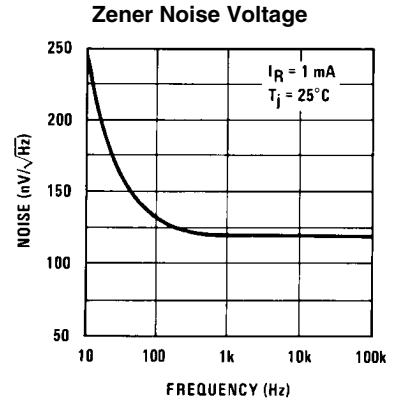
**Note 5:** Pre and post irradiation limits are identical to those listed under DC electrical characteristics. These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in Mil-Std-883, Method 1019.

**Note 6:** Low dose rate testing has been performed on a wafer-by-wafer basis, per test method 1019 condition D of MIL-STD-883, with no enhanced low dose rate sensitivity (ELDRS) effect.

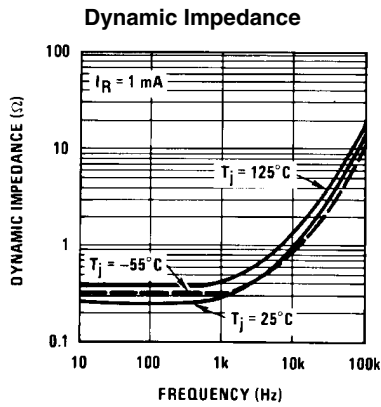
# Typical Performance Characteristics



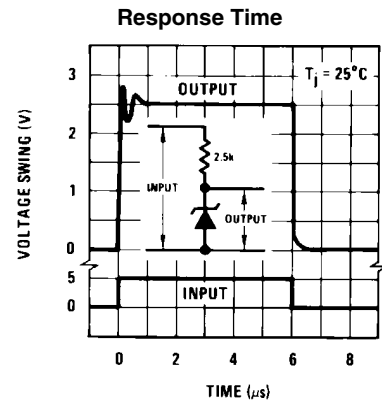
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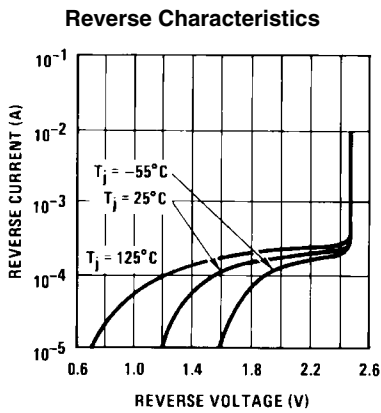
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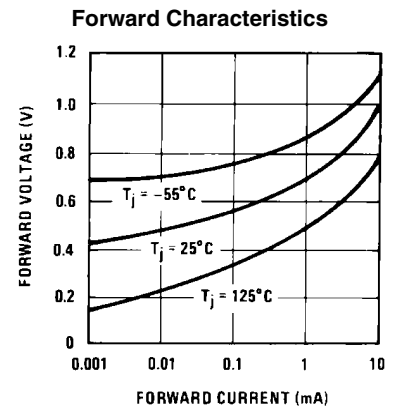
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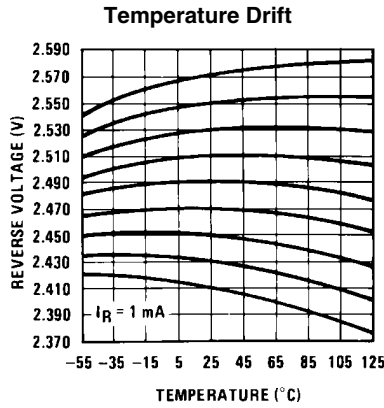
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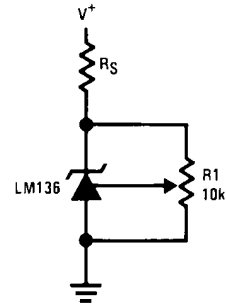
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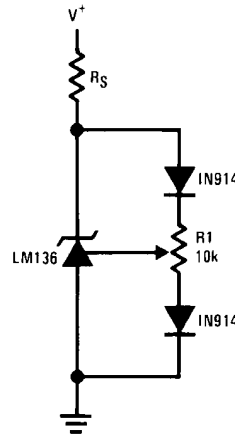
FIGURE 1. LM136 With Pot for Adjustment of Breakdown Voltage (Trim Range = ±120 mV typical)

## Application Hints

The LM136 series voltage references are much easier to use than ordinary zener diodes. Their low impedance and wide operating current range simplify biasing in almost any circuit. Further, either the breakdown voltage or the temperature coefficient can be adjusted to optimize circuit performance.

Figure 1 shows an LM136 with a 10k potentiometer for adjusting the reverse breakdown voltage. With the addition of R1 the breakdown voltage can be adjusted without affecting the temperature coefficient of the device. The adjustment range is usually sufficient to adjust for both the initial device tolerance and inaccuracies in buffer circuitry.

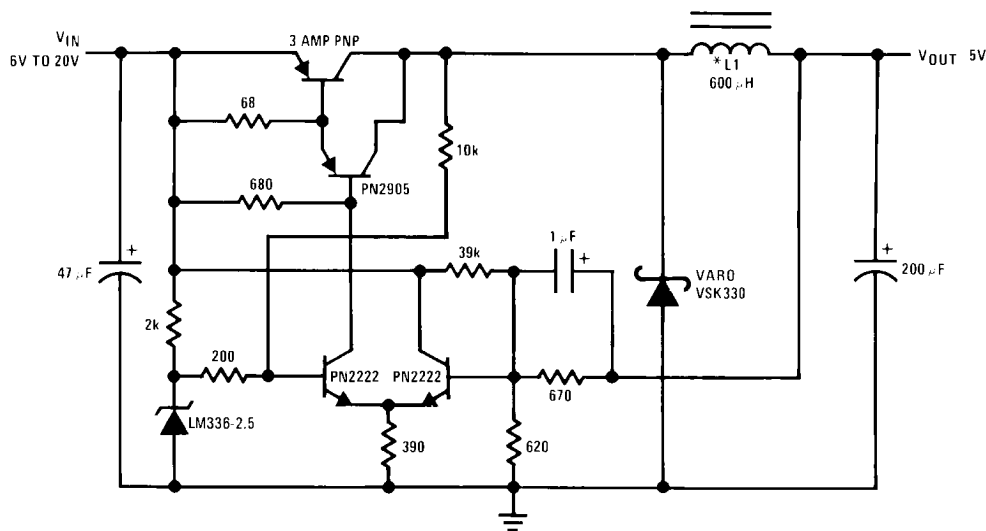
If minimum temperature coefficient is desired, two diodes can be added in series with the adjustment potentiometer as shown in Figure 2. When the device is adjusted to 2.490V the temperature coefficient is minimized. Almost any silicon signal diode can be used for this purpose such as a 1N914, 1N4148 or a 1N457. For proper temperature compensation the diodes should be in the same thermal environment as the LM136. It is usually sufficient to mount the diodes near the LM136 on the printed circuit board. The absolute resistance of R1 is not critical and any value from 2k to 20k will work.



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FIGURE 2. Temperature Coefficient Adjustment (Trim Range = ±70 mV typical)

## Low Cost 2 Amp Switching Regulator†



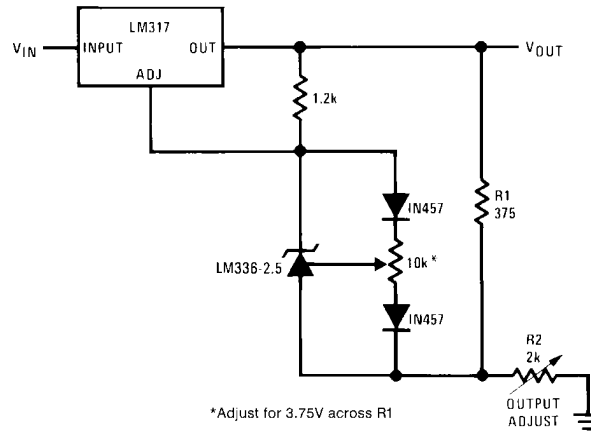
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\*L1 60 turns #16 wire on Arnold Core A-254168-2

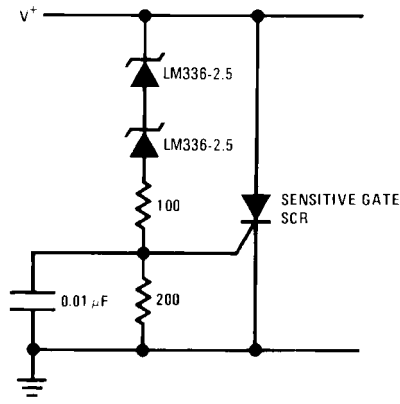
†Efficiency 80%



**Precision Power Regulator with Low Temperature Coefficient**

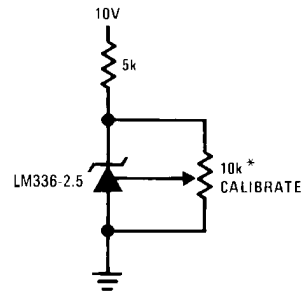


**5V Crowbar**



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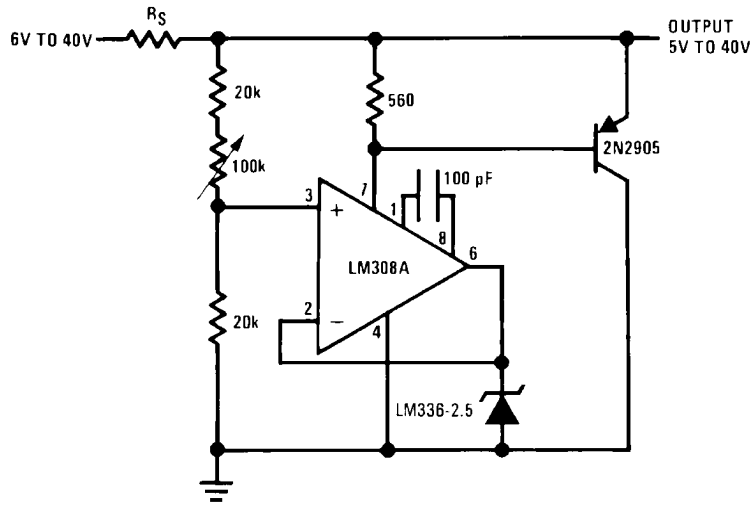
**Trimmed 2.5V Reference with Temperature Coefficient Independent of Breakdown Voltage**



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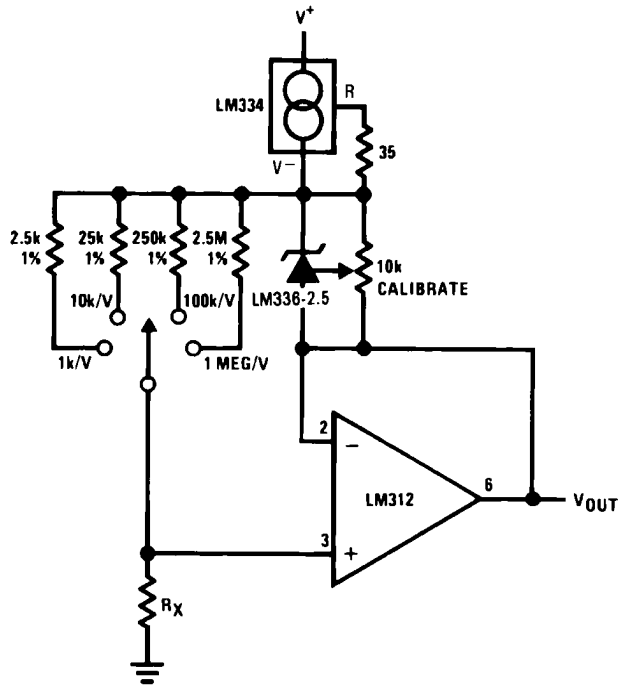
\*Does not affect temperature coefficient

**Adjustable Shunt Regulator**



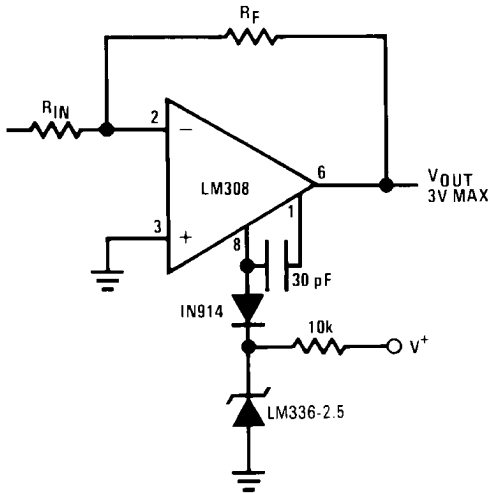
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Linear Ohmmeter



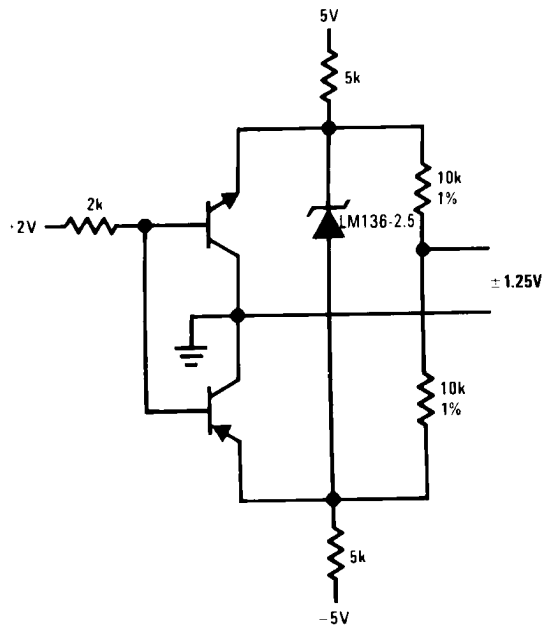
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Op Amp with Output Clamped



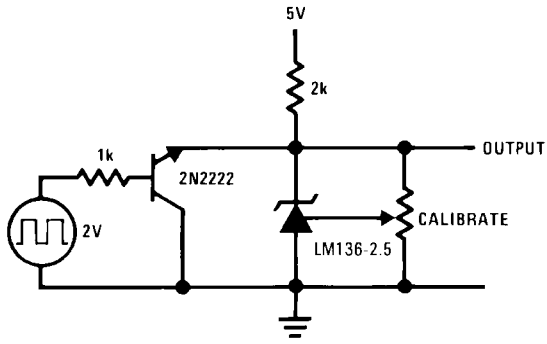
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Bipolar Output Reference



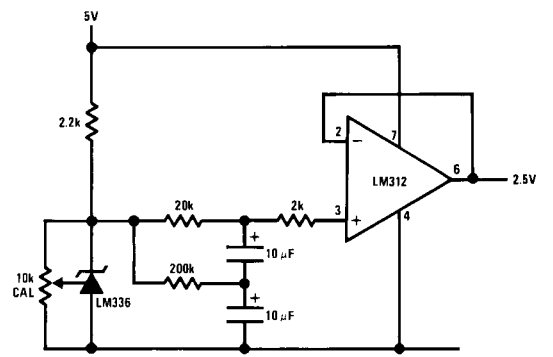
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2.5V Square Wave Calibrator



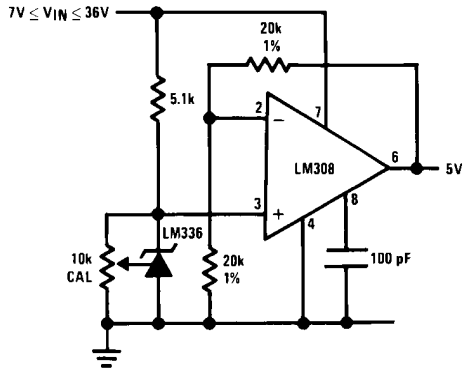
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Low Noise Buffered Reference



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5V Buffered Reference

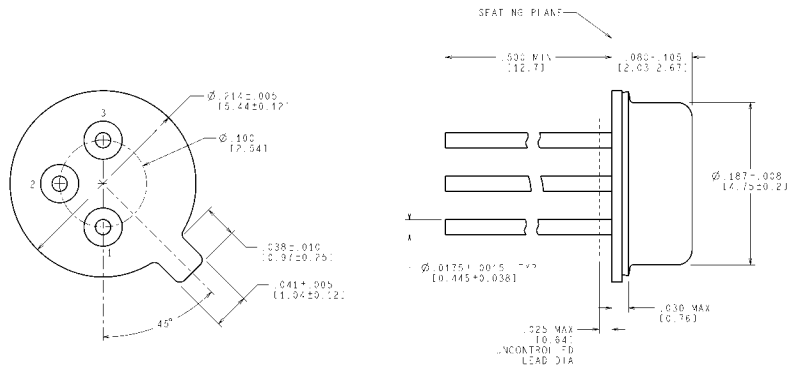


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## Revision History

Date Released	Revision	Section	Originator	Changes
07/06/07	A	New Release, Corporate format	L. Lytle	2 MDS datasheets converted into one corporate datasheet format. MNLM136-2.5-X Rev 0A0 and MNLM136A-2.5-X-RH. The ELDRS Part has also been added. Rev. 0E0 will be archived.

**Physical Dimensions** inches (millimeters) unless otherwise noted



CONTROLLING DIMENSION IS INCH  
VALUES IN [ ] ARE IN MILLIMETERS

H03H (Rev F)

**NS Package Number H03H**

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